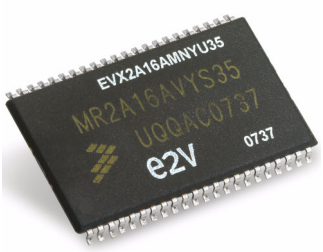
EV2A16A
256K x 16-bit 3.3V Asynchronous Magnetoresistive RAM

Datasheet - *Preliminary Specification*

Features



- **Single 3.3V Power Supply**
- **Industrial Temperature Range (-40°C to 110°C) and Military Temperature Range (-55°C to 125°C)**
- **Symmetrical High-speed Read and Write with Fast Access Time (35 ns)**
- **Flexible Data Bus Control: 8 bit or 16 bit Access**
- **Equal Address and Chip-enable Access Times**
- **Automatic Data Protection with Low-voltage Inhibit Circuitry to Prevent Writes on Power Loss**
- **All Inputs and Outputs are Transistor-transistor Logic (TTL) Compatible**
- **Fully Static Operation**
- **Full Nonvolatile Operation with 20 years Minimum Data Retention**

Introduction

The EV2A16A is a 4,194,304-bit magnetoresistive random access memory (MRAM) device organized as 262,144 words of 16 bits. The EV2A16A is equipped with chip enable ($\overline{E}$), write enable ($\overline{W}$), and output enable ($\overline{G}$) pins, allowing for significant system design flexibility without bus contention. Because the EV2A16A has separate byte-enable controls ($\overline{LB}$ and $\overline{UB}$), individual bytes can be written and read.

MRAM is a nonvolatile memory technology that protects data in the event of power loss and does not require periodic refreshing. The EV2A16A is the ideal memory solution for applications that must permanently store and retrieve critical data quickly.

The EV2A16A is available in a 400-mil, 44-lead plastic small-outline TSOP type-II package with an industry-standard center power and ground SRAM pinout.

The EV2A16A is available in Industrial (-40°C to 110°C) and Military (-55°C to +125°C) temperature ranges.

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for the latest version of the datasheet

1. Device Pin Assignment

Figure 1-1. Block Diagram

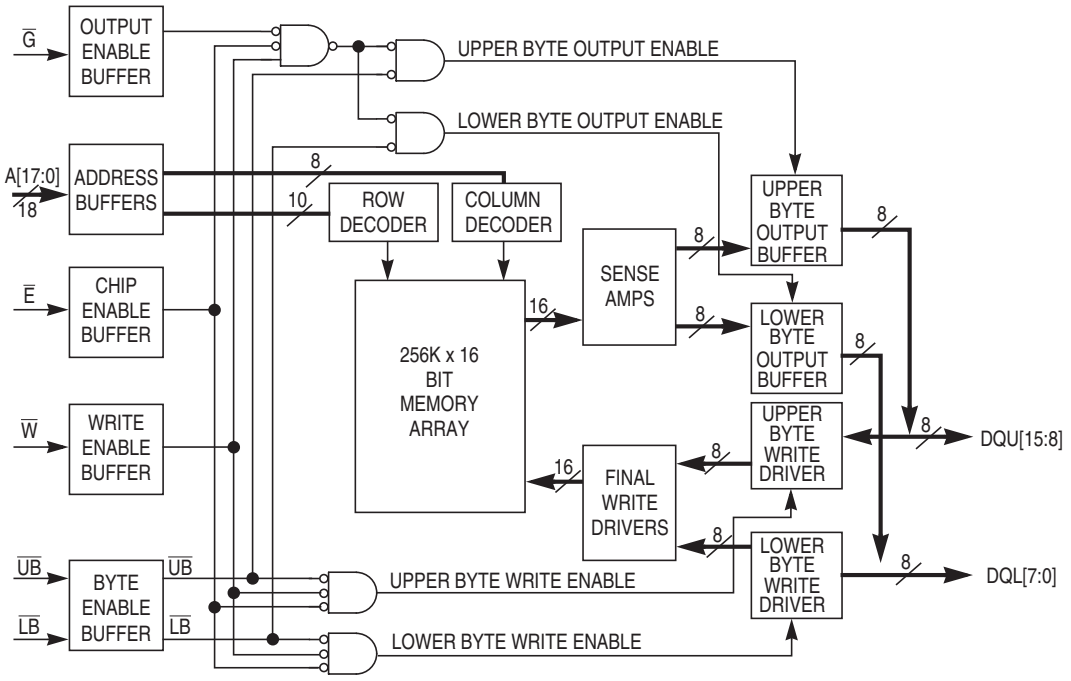


Figure 1-2. EV2A16A in 44-Pin TSOP Type II Package

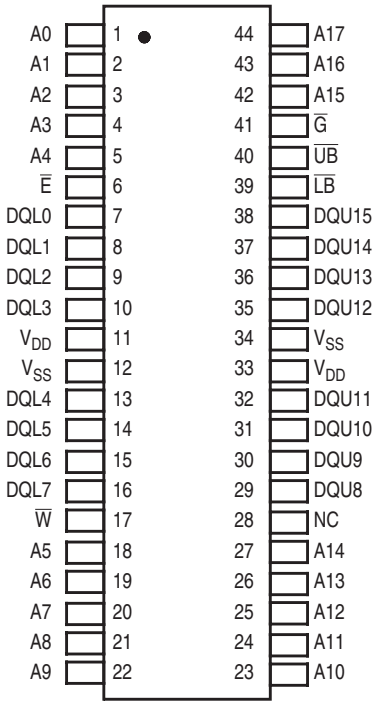


Table 1-1. Pin Functions

Signal Name	Function
A[17:0]	Address input
$\overline{E}$	Chip enable
$\overline{W}$	Write enable
$\overline{G}$	Output enable
$\overline{UB}$	Upper byte select
$\overline{LB}$	Lower byte select
DQL[7:0]	Data I/O, lower byte
DQU[15:8]	Data I/O, upper byte
V_{DD}	Power supply
V_{SS}	Ground
NC	Do not connect this pin

Table 1-2. Operating Modes

$\overline{E}$(1)	$\overline{G}$(1)	$\overline{W}$(1)	$\overline{LB}$(1)	$\overline{UB}$(1)	Mode	V_{DD} Current	DQL[7:0](2)	DQU[15:8](2)
H	X	X	X	X	Not selected	I_{SB1}, I_{SB2}	Hi-Z	Hi-Z
L	H	H	X	X	Output disabled	I_{DDR}	Hi-Z	Hi-Z
L	X	X	H	H	Output disabled	I_{DDR}	Hi-Z	Hi-Z
L	L	H	L	H	Lower byte read	I_{DDR}	D_{Out}	Hi-Z
L	L	H	H	L	Upper byte read	I_{DDR}	Hi-Z	D_{Out}
L	L	H	L	L	Word read	I_{DDR}	D_{Out}	D_{Out}
L	X	L	L	H	Lower byte write	I_{DDW}	D_{In}	Hi-Z
L	X	L	H	L	Upper byte write	I_{DDW}	Hi-Z	D_{In}
L	X	L	L	L	Word write	I_{DDW}	D_{In}	D_{In}

Notes: 1. H = high, L = low, X = don't care
2. Hi-Z = high impedance

2. Electrical Specifications

2.1 Absolute Maximum Ratings

This device contains circuitry to protect the inputs against damage caused by high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage greater than maximum rated voltages to these high-impedance (Hi-Z) circuits.

The device also contains protection against external magnetic fields. Precautions should be taken to avoid application of any magnetic field more intense than the maximum field intensity specified in the maximum ratings.

Table 2-1. Absolute Maximum Ratings(1)

Parameter	Symbol	Value	Unit
Supply voltage(2)	V_{DD}	-0.5 to 4.0	V
Voltage on any pin(2)	V_{In}	-0.5 to V_{DD}+ 0.5	V
Output current per pin	I_{Out}	±20	mA
Package power dissipation(3)	P_D	0.600	W
Temperature under bias	T_{Bias}	-55 to 125	°C
Storage temperature	T_{stg}	-65 to 150	°C
Lead temperature during solder (3 minute max)	T_{Lead}	260	°C
Maximum magnetic field during write	H_{max_write}	25	Oe
Maximum magnetic field during read or standby	H_{max_read}	100	Oe

Notes:
1. Permanent device damage may occur if absolute maximum ratings are exceeded. Functional operation should be restricted to recommended operating conditions. Exposure to excessive voltages or magnetic fields could affect device reliability.
2. All voltages are referenced to V_{SS}.
3. Power dissipation capability depends on package characteristics and use environment.

Table 2-2. Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Power supply voltage	V_{DD}	3.0(1)	3.3	3.6	V
Write inhibit voltage	V_{WI}	2.5	2.7	3.0(1)	V
Input high voltage	V_{IH}	2.2	–	V_{DD} + 0.3(2)	V
Input low voltage	V_{IL}	-0.5(3)	–	0.8	V
Operating temperature	T	-40(4) -55(4)		+110(5) +125(5)	°C

Notes: 1. After power up or if V_{DD} falls below V_{WI}, a waiting period of 2 ms must be observed, and $\overline{E}$ and $\overline{W}$ must remain high for 2 ms. Memory is designed to prevent writing for all input pin conditions if V_{DD} falls below minimum V_{WI}.

2. V_{IH} (max) = V_{DD} + 0.3 Vdc; V_{IH} (max) = V_{DD} + 2.0 Vac (pulse width ≤ 10 ns) for I ≤ 20.0 mA.
3. V_{IL} (min) = 0.5 Vdc; V_{IL} (min) = 2.0 Vac (pulse width ≤ 10 ns) for I ≤ 20.0 mA.
4. Ambient temperature
5. Junction temperature

2.2 Direct Current (dc)

Table 2-3. DC Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Input leakage current	$I_{lkg(I)}$	–	–	±1	µA
Output leakage current	$I_{lkg(O)}$	–	–	±1	µA
Output low voltage (I_{OL}= +4 mA) (I_{OL}= +100 µA)	V_{OL}	–	–	0.4 V_{SS} + 0.2	V
Output high voltage (I_{OH}= -4 mA) (I_{OH}= -100 mA)	V_{OH}	2.4 V_{DD} – 0.2	–	–	V

Table 2-4. Power Supply Characteristics

Parameter	Symbol	Typ	Max	Unit
ac active supply current — read modes(1) (I_{Out} = 0 mA, V_{DD} = max)	I_{DDR}	55	80	mA
ac active supply current — write modes(1) (V_{DD} = max) EV2A16AVYS35	I_{DDW}	105	165	mA
ac standby current (V_{DD} = max, $\overline{E}$ = V_{IH}) (no other restrictions on other inputs)	I_{SB1}	18	28	mA
CMOS standby current ($\overline{E}$ ≥ V_{DD} – 0.2V and V_{In} ≤ V_{SS} + 0.2V or ≥ V_{DD} – 0.2V) (V_{DD} = max, f = 0 MHz)	I_{SB2}	9	12	mA

Note: 1. All active current measurements are measured with one address transition per cycle.

Table 2-5. Capacitance[1]

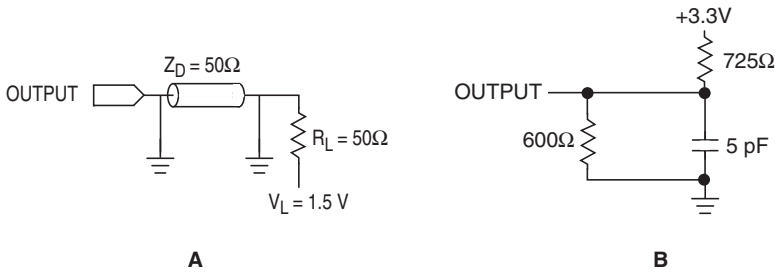
Parameter	Symbol	Typ	Max	Unit
Address input capacitance	C_{In}	–	6	pF
Control input capacitance	C_{In}	–	6	pF
Input/output capacitance	$C_{I/O}$	–	8	pF

Note: 1. f = 1.0 MHz, dV = 3.0V, T_A= 25°C, periodically sampled rather than 100% tested.

Table 2-6. ac Measurement Conditions

Parameter	Value
Logic input timing measurement reference level	1.5V
Logic output timing measurement reference level	1.5V
Logic input pulse levels	0 or 3.0V
Input rise/fall time	2 ns
Output load for low and high impedance parameters	See Figure 2-1A
Output load for all other timing parameters	See Figure 2-1B

Figure 2-1. Output Load for ac Test



2.3 Read Mode

Table 2-7. Read Cycle Timing[1][2]

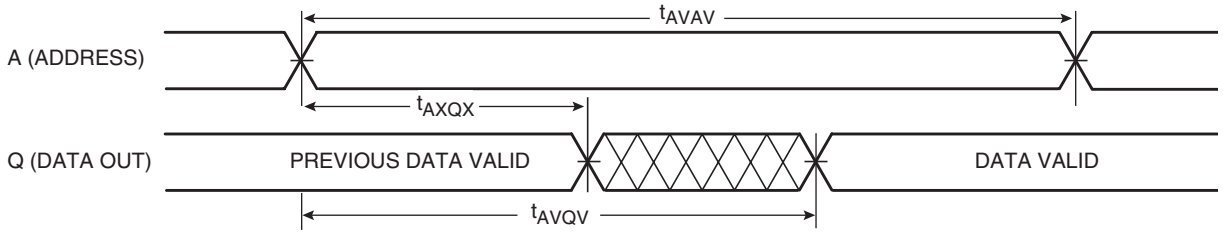
Parameter	Symbol	Min	Max	Unit
Read cycle time	t_{AVAV}	35	–	ns
Address access time	t_{AVQV}	–	35	ns
Enable access time[3]	t_{ELQV}	–	35	ns
Output enable access time	t_{GLQV}	–	15	ns
Byte enable access time	t_{BLQV}	–	15	ns
Output hold from address change	t_{AXQX}	3	–	ns
Enable low to output active[4][5]	t_{ELQX}	3	–	ns
Output enable low to output active[4][5]	t_{GLQX}	0	–	ns
Byte enable low to output active[4][5]	t_{BLQX}	0	–	ns

Table 2-7. Read Cycle Timing[1][2] (Continued)

Parameter	Symbol	Min	Max	Unit
Enable high to output Hi-Z[4][5]	t_{EHQZ}	0	15	ns
Output enable high to output Hi-Z4, 5	t_{GHQZ}	0	10	ns
Byte high to output Hi-Z[4][5]	t_{BHQZ}	0	10	ns

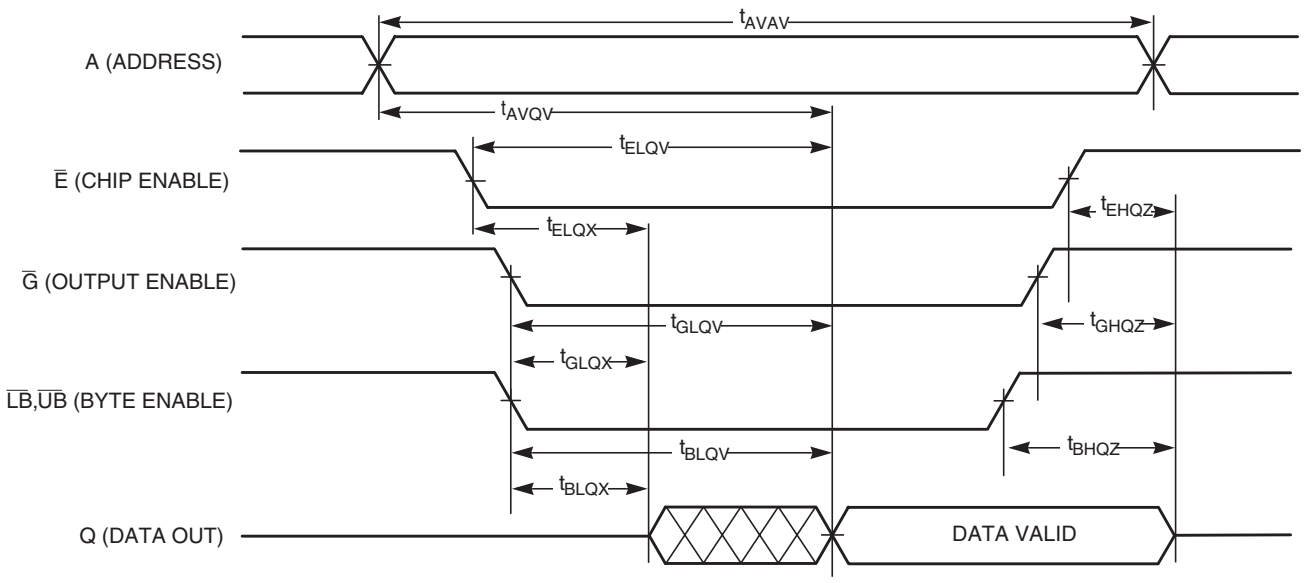
Notes:
1. $\overline{W}$ is high for read cycle.
2. Due to product sensitivities to noise, power supplies must be properly grounded and decoupled, and bus contention conditions must be minimized or eliminated during read and write cycles.
3. Addresses valid before or at the same time $\overline{E}$ goes low.
4. This parameter is sampled and not 100% tested.
5. Transition is measured ±200 mV from steady-state voltage.

Figure 2-2. Read Cycle 1[1]



Note: 1. Device is continuously selected ($\overline{E} \le V_{IL}$, $\overline{G} \le V_{IL}$)

Figure 2-3. Read Cycle 2



2.4 Write Mode

Table 2-8. Write Cycle Timing 1 ($\overline{W}$ Controlled)[1][2][3][4][5]

Parameter	Symbol	Min	Max	Unit
Write cycle time[6]	t_{AVAV}	35	–	ns
Address set-up time	t_{AVWL}	0	–	ns
Address valid to end of write ($\overline{G}$ high)	t_{AVWH}	18	–	ns
Address valid to end of write ($\overline{G}$ low)	t_{AVWH}	20	–	ns
Write pulse width ($\overline{G}$ high)	t_{WLWH} t_{WLEH}	15	–	ns
Write pulse width ($\overline{G}$ low)	t_{WLWH} t_{WLEH}	15	–	ns
Data valid to end of write	t_{DVWH}	10	–	ns
Data hold time	t_{WHDX}	0	–	ns
Write low to data Hi-Z[7][8][9]	t_{WLQZ}	0	12	ns
Write high to output active[7][8][9]	t_{WHQX}	3	–	ns
Write recovery time	t_{WHAX}	12	–	ns

Notes:
1. A write occurs during the overlap of $\overline{E}$ low and $\overline{W}$ low.
2. Due to product sensitivities to noise, power supplies must be properly grounded and decoupled and bus contention conditions must be minimized or eliminated during read and write cycles.
3. If $\overline{G}$ goes low at the same time or after $\overline{W}$ goes low, the output will remain in a high-impedance state.
4. After $\overline{W}$, $\overline{E}$, or $\overline{UB}$/$\overline{LB}$ has been brought high, the signal must remain in steady-state high for a minimum of 2 ns.
5. The minimum time between $\overline{E}$ being asserted low in one cycle to $\overline{E}$ being asserted low in a subsequent cycle is the same as the minimum cycle time allowed for the device.
6. All write cycle timings are referenced from the last valid address to the first transition address.
7. This parameter is sampled and not 100% tested.
8. Transition is measured ±200 mV from steady-state voltage.
9. At any given voltage or temperature, t_{WLQZ} max < t_{WHQX} min.

Figure 2-4. Write Cycle 1 ($\overline{W}$ controlled)

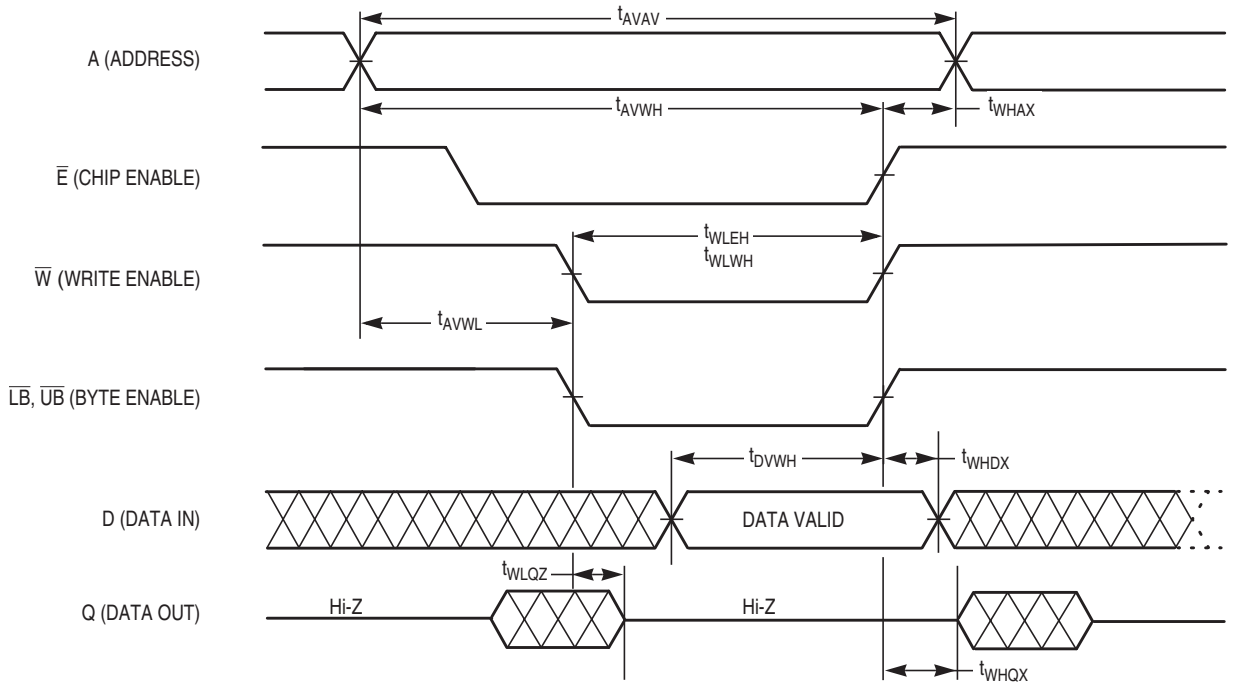


Table 2-9. Write Cycle Timing 2 ($\overline{E}$ Controlled)[(1)(2)(3)(4)(5)]

Parameter	Symbol	Min	Max	Unit
Write cycle time[(6)]	t_{AVAV}	35	–	ns
Address set-up time	t_{AVEL}	0	–	ns
Address valid to end of write ($\overline{G}$ high)	t_{AVEH}	18	–	ns
Address valid to end of write ($\overline{G}$ low)	t_{AVEH}	20	–	ns
Enable to end of write ($\overline{G}$ high)	t_{ELEH} t_{ELWH}	15	–	ns
Enable to end of write ($\overline{G}$ low)[(7)(8)]	t_{ELEH} t_{ELWH}	15	–	ns
Data valid to end of write	t_{DVEH}	10	–	ns
Data hold time	t_{EHDX}	0	–	ns
Write recovery time	t_{EHAX}	12	–	ns

Notes:
1. A write occurs during the overlap of $\overline{E}$ low and $\overline{W}$ low.
2. Due to product sensitivities to noise, power supplies must be properly grounded and decoupled and bus contention conditions must be minimized or eliminated during read and write cycles.
3. If $\overline{G}$ goes low at the same time or after $\overline{W}$ goes low, the output will remain in a high-impedance state.
4. After $\overline{W}$, $\overline{E}$, or $\overline{UB}$/$\overline{LB}$ has been brought high, the signal must remain in steady-state high for a minimum of 2 ns.
5. The minimum time between $\overline{E}$ being asserted low in one cycle to $\overline{E}$ being asserted low in a subsequent cycle is the same as the minimum cycle time allowed for the device.
6. All write cycle timings are referenced from the last valid address to the first transition address.
7. If $\overline{E}$ goes low at the same time or after $\overline{W}$ goes low, the output will remain in a high-impedance state.
8. If $\overline{E}$ goes high at the same time or before $\overline{W}$ goes high, the output will remain in a high-impedance state.

Figure 2-5. Write Cycle 2 ($\overline{E}$ Controlled)

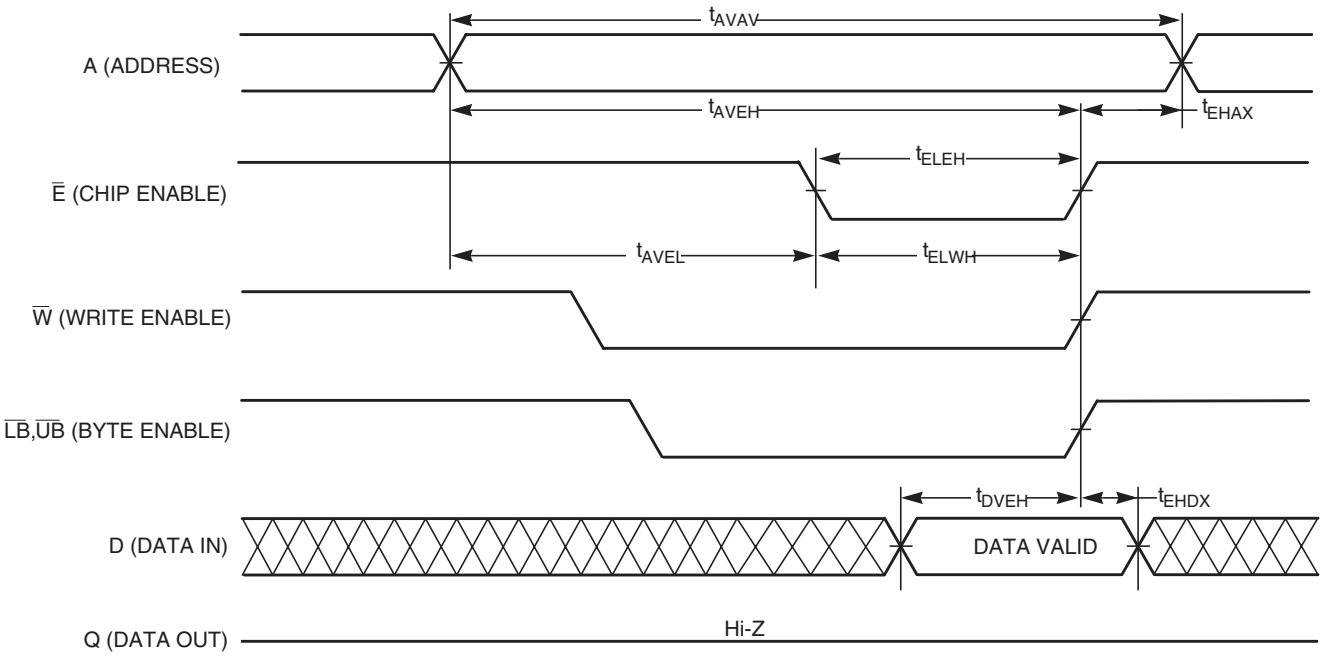
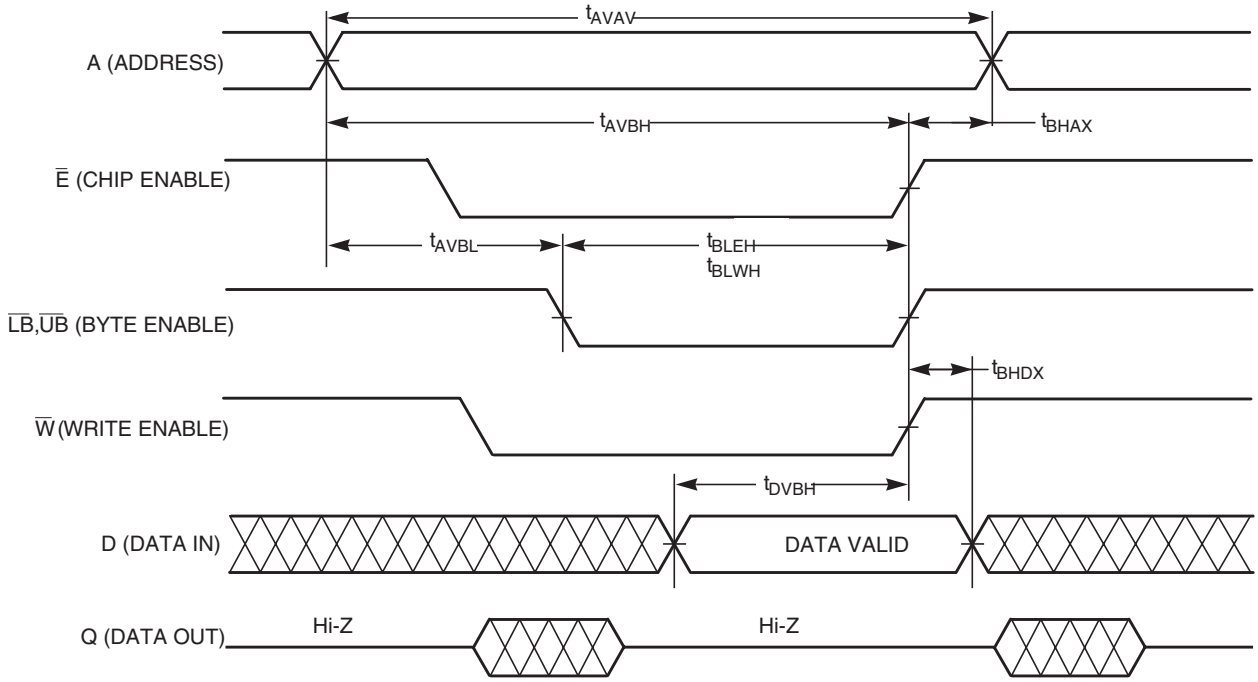


Table 2-10. Write Cycle Timing 3 ($\overline{LB}$/$\overline{UB}$ Controlled)[(1)(2)(3)(4)(5)(6)]

Parameter	Symbol	Min	Max	Unit
Write cycle time[(7)]	t_{AVAV}	35	–	ns
Address set-up time	t_{AVBL}	0	–	ns
Address valid to end of write ($\overline{G}$ high)	t_{AVBH}	18	–	ns
Address valid to end of write ($\overline{G}$ low)	t_{AVBH}	20	–	ns
Byte pulse width ($\overline{G}$ high)	t_{BLEH} t_{BLWH}	15	–	ns
Byte pulse width ($\overline{G}$ low)	t_{BLEH} t_{BLWH}	15	–	ns
Data valid to end of write	t_{DVBH}	10	–	ns
Data hold time	t_{BHDX}	0	–	ns
Write recover time	t_{BHAX}	12	–	ns

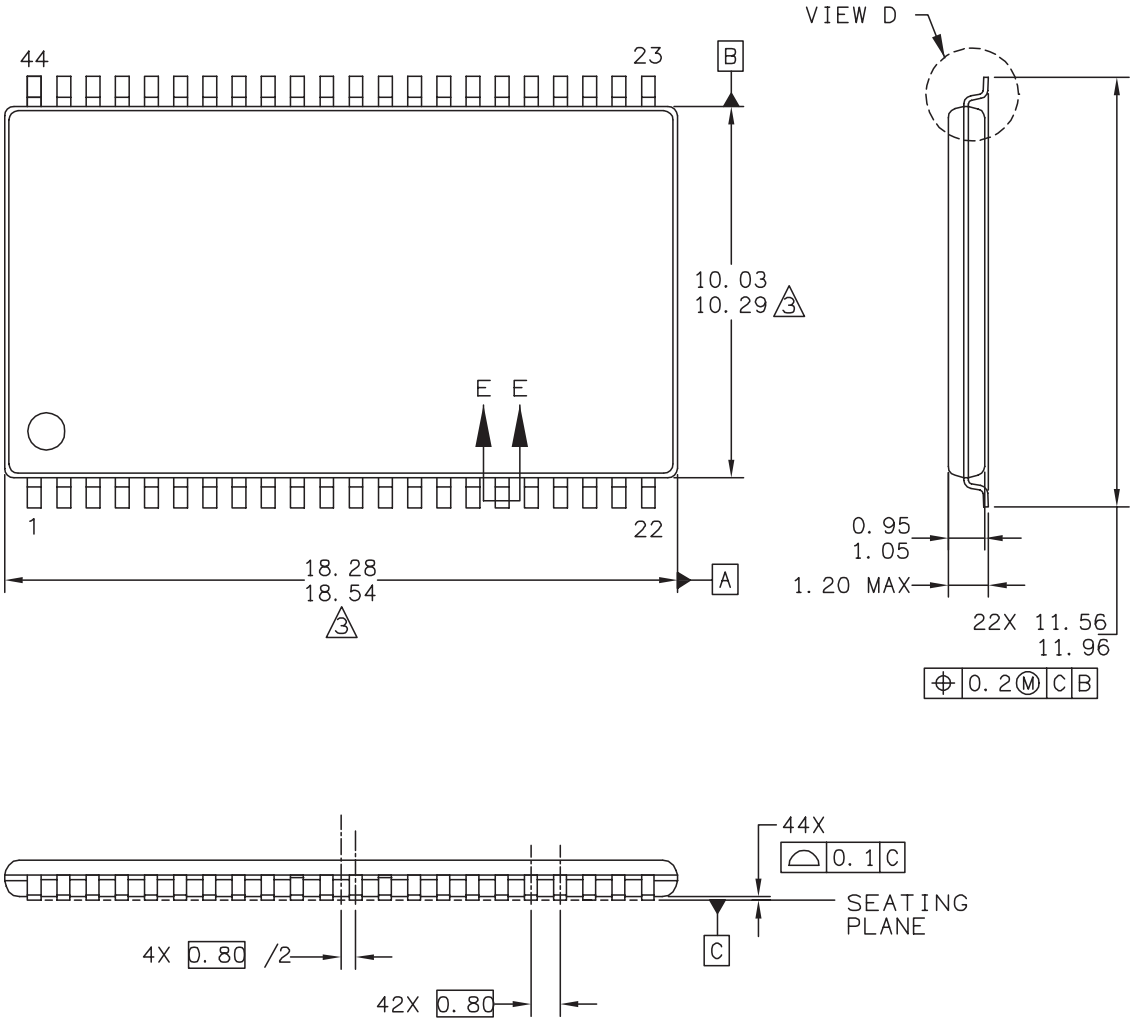
Notes:
1. A write occurs during the overlap of $\overline{E}$ low and $\overline{W}$ low.
2. Due to product sensitivities to noise, power supplies must be properly grounded and decoupled and bus contention conditions must be minimized or eliminated during read and write cycles.
3. If G goes low at the same time or after $\overline{W}$ goes low, the output will remain in a high-impedance state.
4. After $\overline{W}$, $\overline{E}$, or $\overline{UB}$/$\overline{LB}$ has been brought high, the signal must remain in steady-state high for a minimum of 2 ns.
5. If both byte control signals are asserted, the two signals must have no more than 2 ns skew between them.
6. The minimum time between $\overline{E}$ being asserted low in one cycle to $\overline{E}$ being asserted low in a subsequent cycle is the same as the minimum cycle time allowed for the device.
7. All write cycle timings are referenced from the last valid address to the first transition address.

Figure 2-6. Write Cycle 3 ($\overline{LB}$/$\overline{UB}$ Controlled)

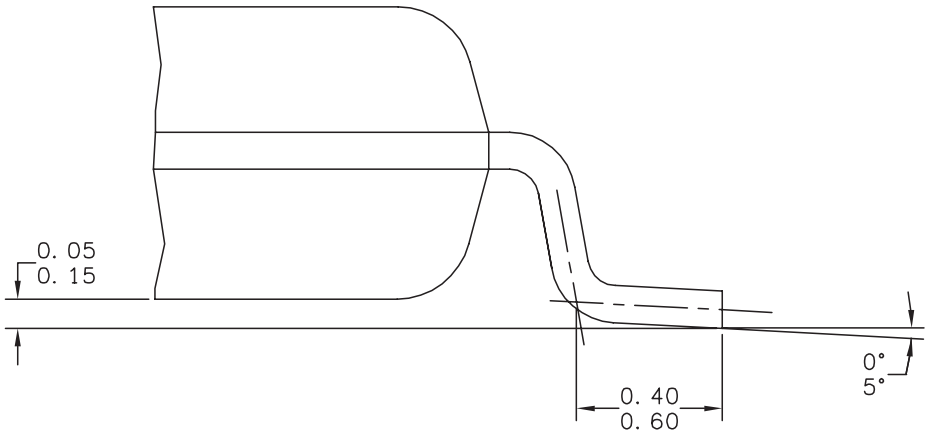


3. Mechanical Drawing

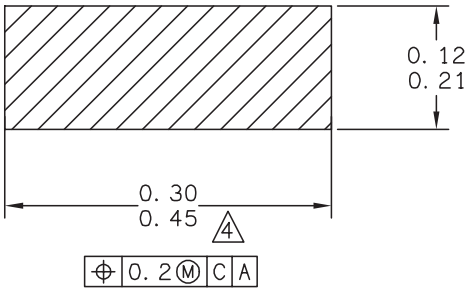
The following pages detail the package available to EV2A16A.



44 LEAD TSOP, TYPE II, .400 WIDE



VIEW D
ROTATED 90° CW



SECTION E–E
40 PLACES

44 LEAD TSOP, TYPE II, .400 WIDE

Notes:
1. Dimensions and tolerancing per asme y14.5m - 1994.
2. Dimensions in millimeters.
3. Dimensions do not include mold protrusion.
   Allowable mold protrusion is 0.15 per side.
4. Dimension does not include DAM bar protrusions.
   DAM bar protrusion shall not cause the lead width to exceed 0.58.

4. Ordering Information

This product is available in Industrial and Military temperature versions.

Figure 4-1. Ordering Information

EV(X)[2]	2	A	16	A	x	N	Y	U	35
	Density Code	Memory Type	I/O Configuration	Revision	Operating Temperature Range	Package Type	RoHS compliance	Upscreening	Timing Set
e2v Prefix	2 = 4 Mb	A = async	16 = 16 bits	A = rev 1	V = -40 to 110˚C M = -55 to 125˚C	(N = TSOP II)	Y: RoHS[3] compliant	U	(35 = 35 ns)

Notes:
1. For availability of the different versions, contact your local e2v sales office.
2. The letter X in the part number designates a "Prototype" product that has not been qualified by e2v. Reliability of a PCX part-number is not guaranteed and such part-number shall not be used in Flight Hardware. Product changes may still occur while shipping prototypes.
3. Lead finishing: pure tin (Sn 99,99%)

5. Document Revision History

Table 5-1 provides a revision history for this hardware specification.

Table 5-1. Document Revision History

Rev. No	Date	Substantive Change(s)
0918A	12/2007	Table 1-2: Changed I_{DDA} to I_{DDR} or I_{DDW} Figure 4-1: Added RoHS compliance status in the part number
0918AX	11/2007	Initial revision.

How to reach us

Home page: www.e2v.com

Sales Office:

Northern Europe

e2v ltd

106 Waterhouse Lane

Chelmsford

Essex CM1 2QU

England

Tel: +44 (0)1245 493493

Fax: +44 (0)1245 492492

E-Mail: enquiries@e2v.com

Southern Europe

e2v sas

16 Burospace

F-91572 Bièvres

Cedex

France

Tel: +33 (0) 1 60 19 55 00

Fax:+33 (0) 1 60 19 55 29

E-Mail: enquiries-fr@e2v.com

Germany and Austria

e2v gmbh

Industriestraße 29

82194 Gröbenzell

Germany

Tel: +49 (0) 842 410 570

Fax:: +49 (0) 842 284 547

E-Mail: enquiries-de@e2v.com

Americas

e2v inc.

4 Westchester Plaza

Elmsford

NY 10523-1482

USA

Tel: +1 (914) 592 6050

Fax:: +1 (914) 592-5148

E-Mail: enquiries-na@e2v.com

Asia Pacific

e2v ltd

11/F,

Onfem Tower,

29 Wyndham Street,Central,

Hong Kong

Tel: +852 3679 364 8/9

Fax: +852 3583 1084

E-Mail: enquiries-ap@e2v.com

Product Contact:

e2v

Avenue de Rochepleine

BP 123 - 38521 Saint-Egrève Cedex

France

Tel: +33 (0)4 76 58 30 00

Hotline:

std-hotline@e2v.com